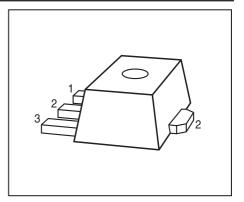


BFQ19S

Low Noise Silicon Bipolar RF Transistor

- For low noise, low distortion broadband amplifiers in antenna and telecommunications systems up to 1.5 GHz at collector currents from 10 mA to 70 mA
- Pb-free (RoHS compliant) package
- Qualification report according to AEC-Q101 available





ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration			Package
BFQ19S	FG	1 = B	2 = C	3 = E	SOT89

Maximum Ratings at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit	
Collector-emitter voltage	V _{CEO}	15	V	
Collector-emitter voltage	V _{CES}	20		
Collector-base voltage	V _{CBO}	20		
Emitter-base voltage	V _{EBO}	3		
Collector current	I _C	120	mA	
Base current	I _B	12		
Total power dissipation ¹⁾	P _{tot}	1	W	
Junction temperature	TJ	150	°C	
Ambient temperature	T _A	-65 150		
Storage temperature	T _{Stg}	-65 150		
Thermal Resistance				

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R _{thJS}	65	K/W

 ${}^{1}T_{S}$ is measured on the collector lead at the soldering point to the pcb

²For the definition of R_{thJS} please refer to Application Note AN077 (Thermal Resistance Calculation)



Parameter	Symbol	Values			Unit
		min.	typ.	max.]
DC Characteristics				-	•
Collector-emitter breakdown voltage	V _{(BR)CEO}	15	-	-	V
<i>I</i> _C = 1 mA, <i>I</i> _B = 0					
Collector-emitter cutoff current	I _{CES}	-	-	10	μA
$V_{\rm CE}$ = 20 V, $V_{\rm BE}$ = 0					
Collector-base cutoff current	I _{CBO}	-	-	100	nA
$V_{\rm CB}$ = 10 V, $I_{\rm E}$ = 0					
Emitter-base cutoff current	I _{EBO}	-	-	100	μA
$V_{\rm EB}$ = 2 V, $I_{\rm C}$ = 0					
DC current gain	h _{FE}	70	100	140	-
$I_{\rm C}$ = 70 mA, $V_{\rm CE}$ = 8 V, pulse measured					

Electrical Characteristics at T_A = 25 °C, unless otherwise specified



Symbol			Values		
	min.	typ.	max.		
g)					
f _T	4	5.5	-	GHz	
C _{cb}	-	1.05	1.35	pF	
C _{ce}	-	0.4	-		
C _{eb}	-	3.9	-		
NF _{min}				dB	
	-	1.8	-		
	-	3	-		
G _{ma}					
	-	11.5	-		
	-	7	-		
S _{21e} ²				dB	
	-	9.5	-		
	-	4	-		
IP ₃	-	32	-	dBm	
P _{-1dB}	-	22	-]	
	g) f_T C_{cb} C_{ce} C_{eb} NF_{min} G_{ma} $ S_{21e} ^2$	min. g) min. f_T 4 C_{cb} - C_{cb} - C_{cb} - C_{cb} - NF_{min} - S_{ma} - $IS_{21e} ^2$ - IP_3 -	min. typ. g) fT 4 5.5 f_T 4 5.5 C_{cb} - 1.05 C_{ce} - 0.4 C_{eb} - 3.9 NF_{min} - 1.8 G_{ma} - 1.8 G_{ma} - 11.5 $IS_{21e} ^2$ - 9.5 IP_3 - 32	min.typ.max.g) f_T 45.5- C_{Cb} -1.051.35 C_{ce} -0.4- C_{eb} -3.9- NF_{min} -1.81.8-3 G_{ma} -11.5- $ S_{21e} ^2$ -9.5- $ P_3$ -32-	

Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

 ${}^{1}\mathrm{G}_{\mathrm{ma}} = |\mathrm{S}_{21}/\mathrm{S}_{12}| \; (\mathrm{k} \cdot (\mathrm{k}^{2} \cdot 1)^{1/2})$

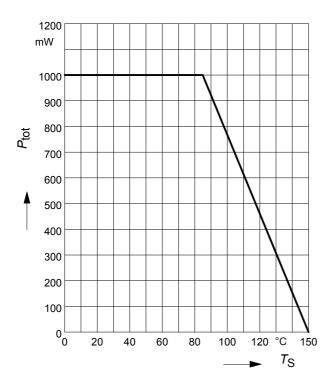
²IP3 value depends on termination of all intermodulation frequency components. Termination used for this measurement is 50Ω from 0.2 MHz to 12 GHz



BFQ19S

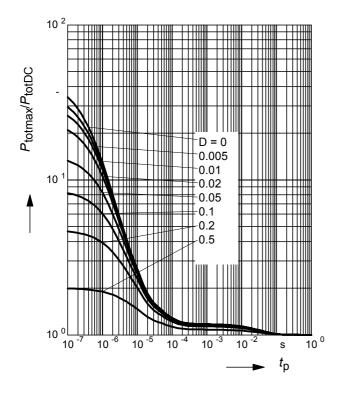
Total power dissipation $P_{tot} = f(T_S)$

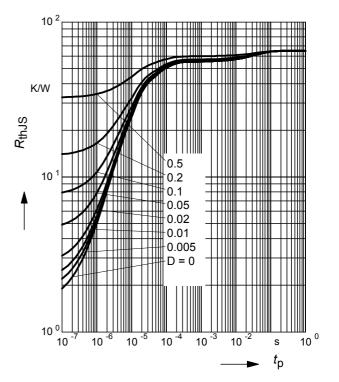
Permissible Pulse Load $R_{\text{thJS}} = f(t_p)$



Permissible Pulse Load

 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_{p})$





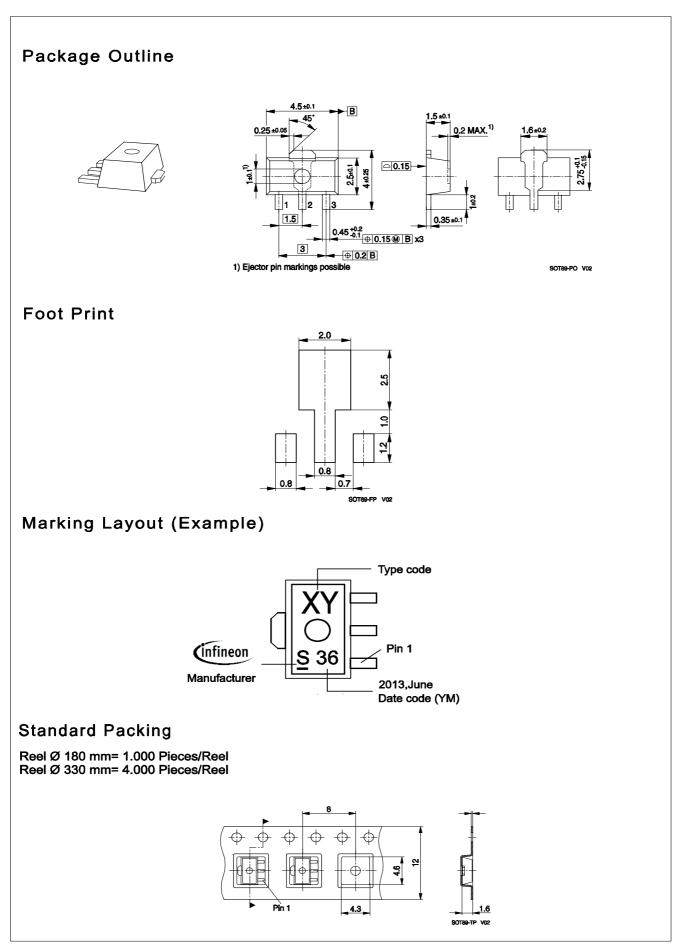




SPICE GP model

For the SPICE model as well as for S-parameters (including noise parameters) please refer to our internet website <u>www.infineon.com/rf.models</u>. Please consult our website and download the latest versions before actually starting your design.









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